

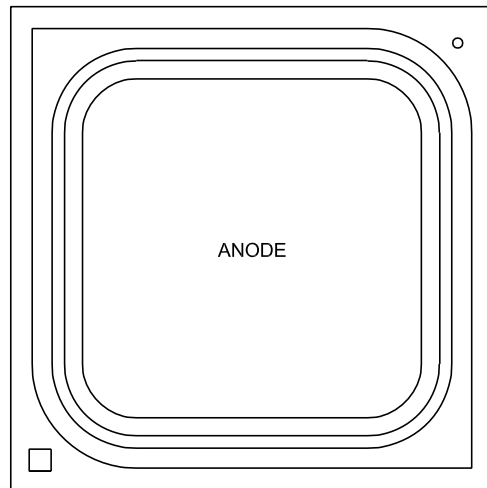
PROCESS CPD82X
Schottky Diode
High Current, Low V_F Schottky Diode Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14.6 x 14.6 MILS
Die Thickness	5.5 MILS
Anode Bonding pad Area	11.8 x 11.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 5 INCH WAFER

80,282

PRINCIPAL DEVICE TYPES

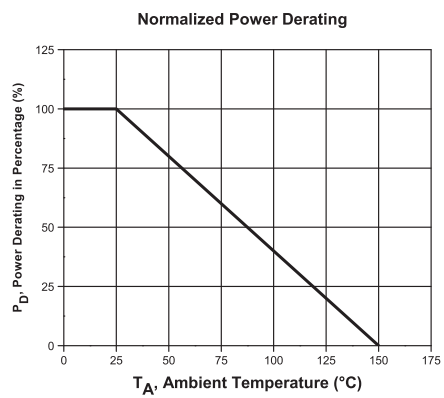
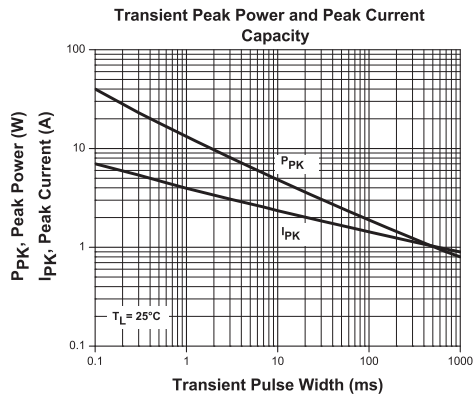
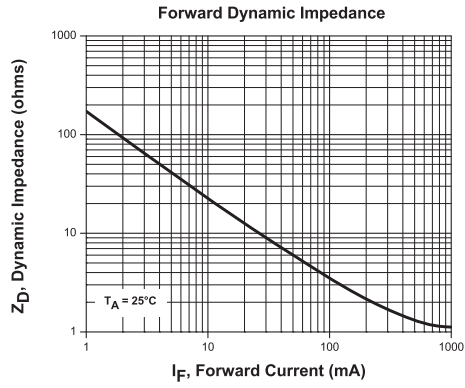
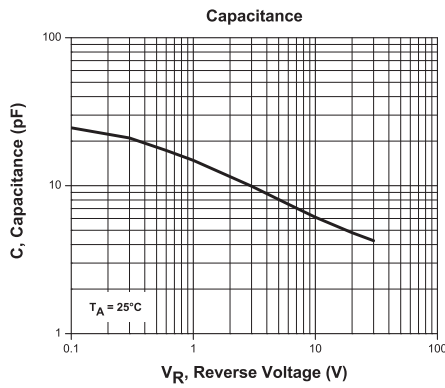
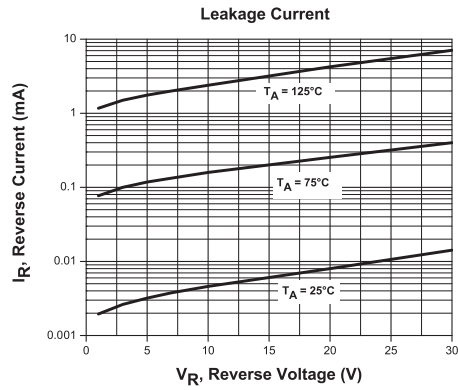
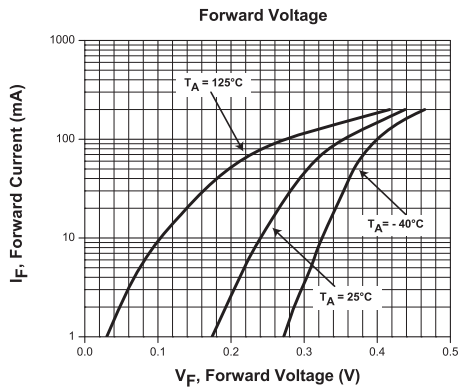
- CMDSH2-3
- CMDSH2-4L
- CMOSH2-4L
- CMUSH2-4L
- CMKSH2-4L
- CMXSH2-4L

R0

R2 (22-March 2010)

PROCESS CPD82X

Typical Electrical Characteristics



R2 (22-March 2010)